In the Claims:

1. (Currently amended) A method for removal of a barrier film on a semiconductor wafer by polishing with a polishing pad and a polishing fluid, the polishing fluid comprising abrasive particles in the range of 0.1% to 5% by weight and an acid consisting of an organic acid or mixture thereof in the range of 0.5-10% by weight in an aqueous solution at ~~basic~~ a pH of 7 to 12 with no addition of an oxidizing agent.

2. (Currently amended) The~~A~~ method as in claim 1, wherein the organic acid is selected from the group consisting of carboxylic acids, hydrocarboxylic acids containing a hydroxyl group, and amino acids.

3. (Currently amended) The~~A~~ method as in claim 2, wherein the organic acid is selected from the group consisting of citric acid, maleic acid, formic acid, acetic acid, propionic acid, butyric acid, valeric acid, acrylic acid, lactic acid, succinic acid malic acid, malonic acid, succinic acid, tartaric acid, phthalic acid, fumaric acid, lactic acid (alpha-hydroxypropionic acid or beta-hydroxypropionic acid), pimelic acid, adipic acid, glutaric acid, oxalic acid, salicylic acid, glycolic acid, tricarballylic acid, and benzoic acid.

4. (Currently amended) The~~A~~ method as in claim ~~2~~1, wherein the organic acid is an amino acid is selected from the group consisting of glutamic acid, glutamic acid hydrochloride, sodium glutaminate monohydrate, glutamine, glutathione, glycylglycine, alanine, beta.-alanine, gamma-aminobutyric acid, epsilon-aminocarproic acid, lysine, lysine hydrochloride, lysine dihydrochloride, lysine picrate, histidine, histidine hydrochloride, histidine dihydrochloride, aspartic acid, aspartic acid monohydrate, potassium aspartate, potassium aspartate trihydrate, tryptophan, threonine, glycine, cystine, cysteine, cysteine hydrochloride monohydrate, oxyproline, isoleucine, leucine, methionine, ornithine hydrochloride, phenylalanine, phenylglycine, proline, serine, tyrosine, valine, and a mixture of these amino acids.

5. (Currently amended) The~~A~~ method as in claim 1, wherein the ~~said~~ abrasive is silicon dioxide.

6. (Currently amended) The~~A~~ method as in claim 3, wherein the organic acid is citric acid.

7. (Currently amended) The~~A~~ method as in claim 4, wherein the amino acid is glutamic acid.

8. (Currently amended) The~~A~~ method as in claim 1 wherein a metal corrosion inhibitor is added to ~~said~~ the polishing solution.

9. (Currently amended) The~~A~~ method as in claim 1 wherein the ~~fluid~~ pH of the polishing fluid is in the range ~~from pH~~of 7 to ~~pH~~ 11.

10. (Withdrawn-currently amended) A polishing fluid for removal of a barrier film on a semiconductor wafer by polishing with a polishing pad and the polishing fluid wherein the polishing fluid comprises abrasive particles in the range of 0.1% to 5% by weight and an acid consisting of an organic acid or mixture thereof in the range of 0.5-10% by weight in an aqueous solution at ~~basic~~ a pH of 7 to 12 with no addition of an oxidizing agent.